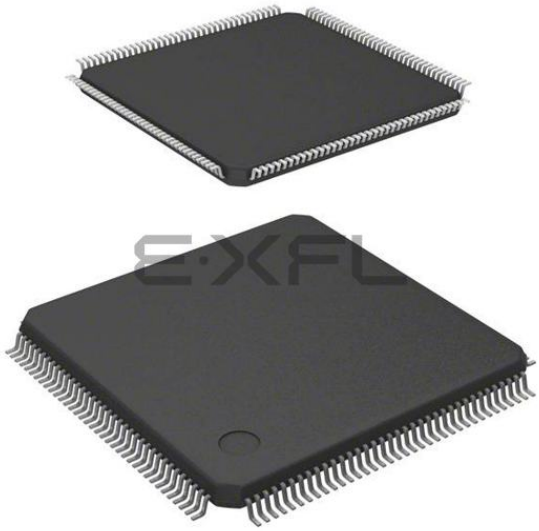

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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, Motor Control PWM, PDR, POR, PVD, PWM, Temp Sensor, WDT
Number of I/O	112
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	48K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 21x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f103zct7tr

Contents

2.3.6 LCD parallel interface

The FSMC can be configured to interface seamlessly with most graphic LCD controllers. It supports the Intel 8080 and Motorola 6800 modes, and is flexible enough to adapt to specific LCD interfaces. This LCD parallel interface capability makes it easy to build cost-effective graphic applications using LCD modules with embedded controllers or high-performance solutions using external controllers with dedicated acceleration.

2.3.7 Nested vectored interrupt controller (NVIC)

The STM32F103xC, STM32F103xD and STM32F103xE performance line embeds a nested vectored interrupt controller able to handle up to 60 maskable interrupt channels (not including the 16 interrupt lines of Cortex®-M3) and 16 priority levels.

- Closely coupled NVIC gives low latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Closely coupled NVIC core interface
- Allows early processing of interrupts
- Processing of *late arriving* higher priority interrupts
- Support for tail-chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

This hardware block provides flexible interrupt management features with minimal interrupt latency.

2.3.8 External interrupt/event controller (EXTI)

The external interrupt/event controller consists of 19 edge detector lines used to generate interrupt/event requests. Each line can be independently configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 112 GPIOs can be connected to the 16 external interrupt lines.

2.3.9 Clocks and startup

System clock selection is performed on startup, however the internal RC 8 MHz oscillator is selected as default CPU clock on reset. An external 4-16 MHz clock can be selected, in which case it is monitored for failure. If failure is detected, the system automatically switches back to the internal RC oscillator. A software interrupt is generated if enabled. Similarly, full interrupt management of the PLL clock entry is available when necessary (for example with failure of an indirectly used external oscillator).

Several prescalers allow the configuration of the AHB frequency, the high speed APB (APB2) and the low speed APB (APB1) domains. The maximum frequency of the AHB and the high speed APB domains is 72 MHz. The maximum allowed frequency of the low speed APB domain is 36 MHz. See *Figure 2* for details on the clock tree.

Table 5. High-density STM32F103xC/D/E pin definitions (continued)

Pins						Pin name	Type(1)	I / O Level(2)	Main function(3) (after reset)	Alternate functions(4)	
LFBGA144	LFBGA100	WLCSP64	LQFP64	LQFP100	LQFP144					Default	Remap
H3	E2	D6	10	17	28	PC2	I/O	-	PC2	ADC123_IN12	-
H4	F3	-	11	18	29	PC3(7)	I/O	-	PC3	ADC123_IN13	-
J1	G1	E7	12	19	30	V_{SSA}	S	-	V_{SSA}	-	-
K1	H1	-	-	20	31	V_{REF-}	S	-	V_{REF-}	-	-
L1	J1	F7 (8)	-	21	32	V_{REF+}	S	-	V_{REF+}	-	-
M1	K1	G8	13	22	33	V_{DDA}	S	-	V_{DDA}	-	-
J2	G2	F6	14	23	34	PA0-WKUP	I/O	-	PA0	WKUP/USART2_CTS(9) ADC123_IN0 TIM2_CH1_ETR TIM5_CH1/TIM8_ETR	-
K2	H2	E6	15	24	35	PA1	I/O	-	PA1	USART2_RTS(9) ADC123_IN1/ TIM5_CH2/TIM2_CH2(9)	-
L2	J2	H8	16	25	36	PA2	I/O	-	PA2	USART2_TX(9)/TIM5_CH3 ADC123_IN2/ TIM2_CH3 (9)	-
M2	K2	G7	17	26	37	PA3	I/O	-	PA3	USART2_RX(9)/TIM5_CH4 ADC123_IN3/TIM2_CH4(9)	-
G4	E4	F5	18	27	38	V_{SS_4}	S	-	V_{SS_4}	-	-
F4	F4	G6	19	28	39	V_{DD_4}	S	-	V_{DD_4}	-	-
J3	G3	H7	20	29	40	PA4	I/O	-	PA4	SPI1_NSS(9)/ USART2_CK(9) DAC_OUT1/ADC12_IN4	-
K3	H3	E5	21	30	41	PA5	I/O	-	PA5	SPI1_SCK(9) DAC_OUT2 ADC12_IN5	-
L3	J3	G5	22	31	42	PA6	I/O	-	PA6	SPI1_MISO(9) TIM8_BKIN/ADC12_IN6 TIM3_CH1(9)	TIM1_BKIN
M3	K3	G4	23	32	43	PA7	I/O	-	PA7	SPI1_MOSI(9)/ TIM8_CH1N/ADC12_IN7 TIM3_CH2(9)	TIM1_CH1N
J4	G4	H6	24	33	44	PC4	I/O	-	PC4	ADC12_IN14	-
K4	H4	H5	25	34	45	PC5	I/O	-	PC5	ADC12_IN15	-

Table 5. High-density STM32F103xC/D/E pin definitions (continued)

Pins						Pin name	Type(1)	I / O Level(2)	Main function(3) (after reset)	Alternate functions(4)	
LFBGA144	LFBGA100	WLCSP64	LQFP64	LQFP100	LQFP144					Default	Remap
L4	J4	H4	26	35	46	PB0	I/O	-	PB0	ADC12_IN8/TIM3_CH3 TIM8_CH2N	TIM1_CH2N
M4	K4	F4	27	36	47	PB1	I/O	-	PB1	ADC12_IN9/TIM3_CH4(9) TIM8_CH3N	TIM1_CH3N
J5	G5	H3	28	37	48	PB2	I/O	FT	PB2/BOOT1	-	-
M5	-	-	-	-	49	PF11	I/O	FT	PF11	FSMC_NIOS16	-
L5	-	-	-	-	50	PF12	I/O	FT	PF12	FSMC_A6	-
H5	-	-	-	-	51	V_{SS_6}	S	-	V_{SS_6}	-	-
G5	-	-	-	-	52	V_{DD_6}	S	-	V_{DD_6}	-	-
K5	-	-	-	-	53	PF13	I/O	FT	PF13	FSMC_A7	-
M6	-	-	-	-	54	PF14	I/O	FT	PF14	FSMC_A8	-
L6	-	-	-	-	55	PF15	I/O	FT	PF15	FSMC_A9	-
K6	-	-	-	-	56	PG0	I/O	FT	PG0	FSMC_A10	-
J6	-	-	-	-	57	PG1	I/O	FT	PG1	FSMC_A11	-
M7	H5	-	-	38	58	PE7	I/O	FT	PE7	FSMC_D4	TIM1_ETR
L7	J5	-	-	39	59	PE8	I/O	FT	PE8	FSMC_D5	TIM1_CH1N
K7	K5	-	-	40	60	PE9	I/O	FT	PE9	FSMC_D6	TIM1_CH1
H6	-	-	-	-	61	V_{SS_7}	S	-	V_{SS_7}	-	-
G6	-	-	-	-	62	V_{DD_7}	S	-	V_{DD_7}	-	-
J7	G6	-	-	41	63	PE10	I/O	FT	PE10	FSMC_D7	TIM1_CH2N
H8	H6	-	-	42	64	PE11	I/O	FT	PE11	FSMC_D8	TIM1_CH2
J8	J6	-	-	43	65	PE12	I/O	FT	PE12	FSMC_D9	TIM1_CH3N
K8	K6	-	-	44	66	PE13	I/O	FT	PE13	FSMC_D10	TIM1_CH3
L8	G7	-	-	45	67	PE14	I/O	FT	PE14	FSMC_D11	TIM1_CH4
M8	H7	-	-	46	68	PE15	I/O	FT	PE15	FSMC_D12	TIM1_BKIN
M9	J7	G3	29	47	69	PB10	I/O	FT	PB10	I2C2_SCL/USART3_TX(9)	TIM2_CH3
M10	K7	F3	30	48	70	PB11	I/O	FT	PB11	I2C2_SDA/USART3_RX(9)	TIM2_CH4
H7	E7	H2	31	49	71	V_{SS_1}	S	-	V_{SS_1}	-	-
G7	F7	H1	32	50	72	V_{DD_1}	S	-	V_{DD_1}	-	-

Figure 14. Typical current consumption in Run mode versus frequency (at 3.6 V) - code with data processing running from RAM, peripherals enabled

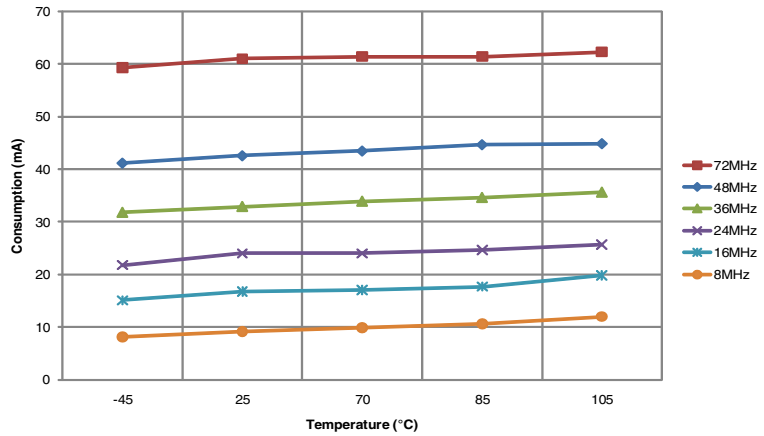


Figure 15. Typical current consumption in Run mode versus frequency (at 3.6 V)- code with data processing running from RAM, peripherals disabled

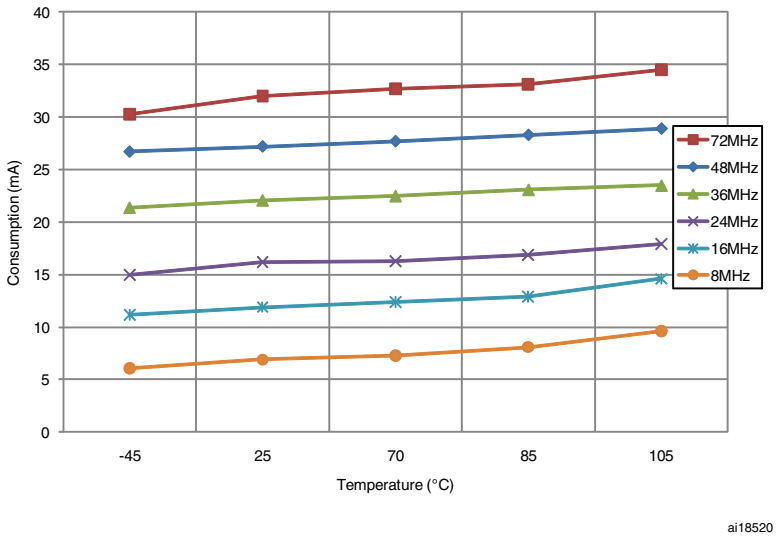


Table 17. Typical and maximum current consumptions in Stop and Standby modes

Symbol	Parameter	Conditions	Typ(1)			Max		Unit
			V_{DD}/V_{BAT} = 2.0 V	V_{DD}/V_{BAT} = 2.4 V	V_{DD}/V_{BAT} = 3.3 V	T_A = 85 °C	T_A = 105 °C	
I_{DD}	Supply current in Stop mode	Regulator in run mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	-	34.5	35	379	1130	µA
		Regulator in low-power mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	-	24.5	25	365	1110	
	Supply current in Standby mode	Low-speed internal RC oscillator and independent watchdog ON	-	3	3.8	-	-	
		Low-speed internal RC oscillator ON, independent watchdog OFF	-	2.8	3.6	-	-	
		Low-speed internal RC oscillator and independent watchdog OFF, low-speed oscillator and RTC OFF	-	1.9	2.1	5(2)	6.5(2)	
I_{DD_VBAT}	Backup domain supply current	Low-speed oscillator and RTC ON	1.05	1.1	1.4	2(2)	2.3(2)	

1. Typical values are measured at T_A = 25 °C.
2. Guaranteed by characterization results.

Figure 16. Typical current consumption on V_{BAT} with RTC on vs. temperature at different V_{BAT} values

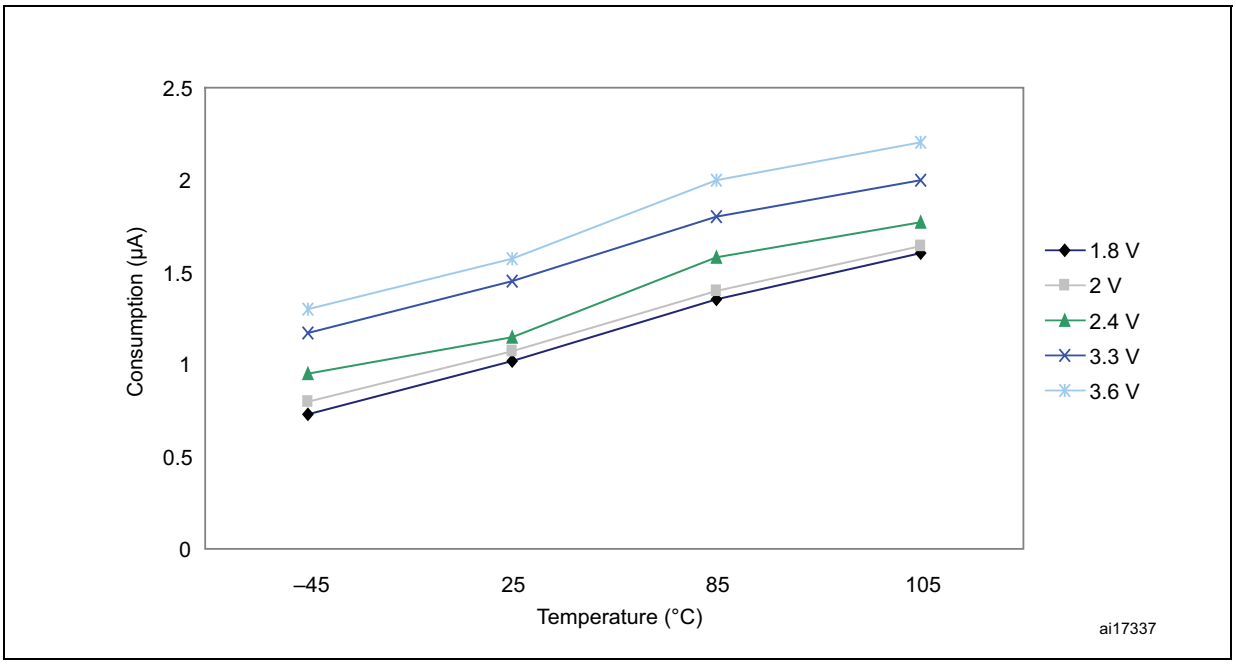
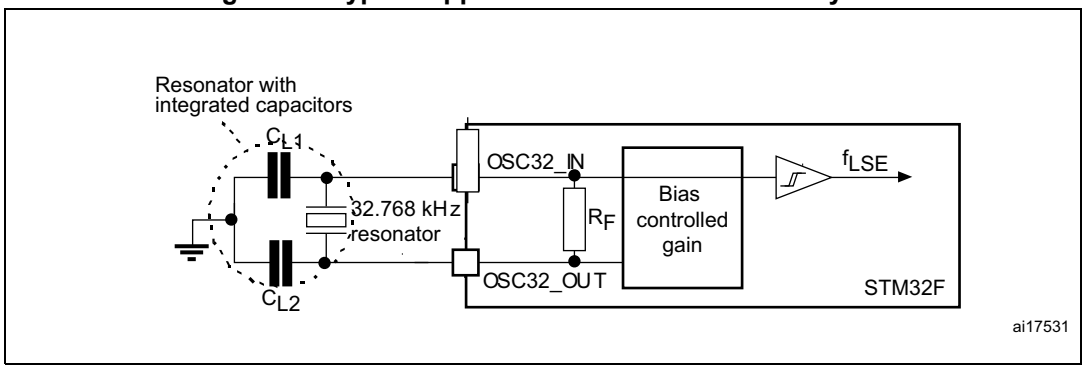


Table 19. Typical current consumption in Sleep mode, code running from Flash or RAM

Symbol	Parameter	Conditions	f_{HCLK}	Typ(1)		Unit
				All peripherals enabled(2)	All peripherals disabled	
I_{DD}	Supply current in Sleep mode	External clock(3)	72 MHz	29.5	6.4	mA
			48 MHz	20	4.6	
			36 MHz	15.1	3.6	
			24 MHz	10.4	2.6	
			16 MHz	7.2	2	
			8 MHz	3.9	1.3	
			4 MHz	2.6	1.2	
			2 MHz	1.85	1.15	
			1 MHz	1.5	1.1	
			500 kHz	1.3	1.05	
			125 kHz	1.2	1.05	
		Running on high speed internal RC (HSI), AHB prescaler used to reduce the frequency	64 MHz	25.6	5.1	
			48 MHz	19.4	4	
			36 MHz	14.5	3	
			24 MHz	9.8	2	
			16 MHz	6.6	1.4	
			8 MHz	3.3	0.7	
			4 MHz	2	0.6	
			2 MHz	1.25	0.55	
			1 MHz	0.9	0.5	
			500 kHz	0.7	0.45	
			125 kHz	0.6	0.45	

1. Typical values are measures at T_A = 25 °C, V_{DD} = 3.3 V.
2. Add an additional power consumption of 0.8 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is on (ADON bit is set in the ADC_CR2 register).
3. External clock is 8 MHz and PLL is on when f_{HCLK} > 8 MHz.

Figure 23. Typical application with a 32.768 kHz crystal



5.3.7 Internal clock source characteristics

The parameters given in *Table 25* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 10*.

High-speed internal (HSI) RC oscillator

Table 25. HSI oscillator characteristics(1)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
f_{HSI}	Frequency	-		-	8	-	MHz
$DuCy_{(HSI)}$	Duty cycle	-		45	-	55	%
ACC_{HSI}	Accuracy of the HSI oscillator	User-trimmed with the RCC_CR register(2)		-	-	1(3)	%
		Factory-calibrated(4)	T_A = –40 to 105 °C	–2	-	2.5	%
			T_A = –10 to 85 °C	–1.5	-	2.2	%
			T_A = 0 to 70 °C	–1.3	-	2	%
			T_A = 25 °C	–1.1	-	1.8	%
$t_{su(HSI)}$(4)	HSI oscillator startup time	-		1	-	2	µs
$I_{DD(HSI)}$(4)	HSI oscillator power consumption	-		-	80	100	µA

1. V_{DD} = 3.3 V, T_A = –40 to 105 °C unless otherwise specified.
2. Refer to application note AN2868 “STM32F10xxx internal RC oscillator (HSI) calibration” available from the ST website *www.st.com*.
3. Guaranteed by design.
4. Guaranteed by characterization results.

Table 30. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Value	Unit
			Min(1)	
N_{END}	Endurance	T_A = –40 to +85 °C (6 suffix versions) T_A = –40 to +105 °C (7 suffix versions)	10	kcycles
t_{RET}	Data retention	1 kcycle(2) at T_A = 85 °C	30	Years
		1 kcycle(2) at T_A = 105 °C	10	
		10 kcycles(2) at T_A = 55 °C	20	

1. Guaranteed by characterization results.
2. Cycling performed over the whole temperature range.

Table 32. Asynchronous non-multiplexed SRAM/PSRAM/NOR write timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FSMC_NE low time	$3t_{HCLK} - 1$	$3t_{HCLK} + 2$	ns
$t_{v(NWE\_NE)}$	FSMC_NEx low to FSMC_NWE low	$t_{HCLK} - 0.5$	$t_{HCLK} + 1.5$	ns
$t_{w(NWE)}$	FSMC_NWE low time	$t_{HCLK} - 0.5$	$t_{HCLK} + 1.5$	ns
$t_{h(NE\_NWE)}$	FSMC_NWE high to FSMC_NE high hold time	t_{HCLK}	-	ns
$t_{v(A\_NE)}$	FSMC_NEx low to FSMC_A valid	-	7.5	ns
$t_{h(A\_NWE)}$	Address hold time after FSMC_NWE high	t_{HCLK}	-	ns
$t_{v(BL\_NE)}$	FSMC_NEx low to FSMC_BL valid	-	0	ns
$t_{h(BL\_NWE)}$	FSMC_BL hold time after FSMC_NWE high	$t_{HCLK} - 0.5$	-	ns
$t_{v(Data\_NE)}$	FSMC_NEx low to Data valid	-	$t_{HCLK} + 7$	ns
$t_{h(Data\_NWE)}$	Data hold time after FSMC_NWE high	t_{HCLK}	-	ns
$t_{v(NADV\_NE)}$	FSMC_NEx low to FSMC_NADV low	-	5.5	ns
$t_{w(NADV)}$	FSMC_NADV low time	-	$t_{HCLK} + 1.5$	ns

1. C_L = 15 pF.
2. Guaranteed by characterization results.

Figure 26. Asynchronous multiplexed PSRAM/NOR read waveforms

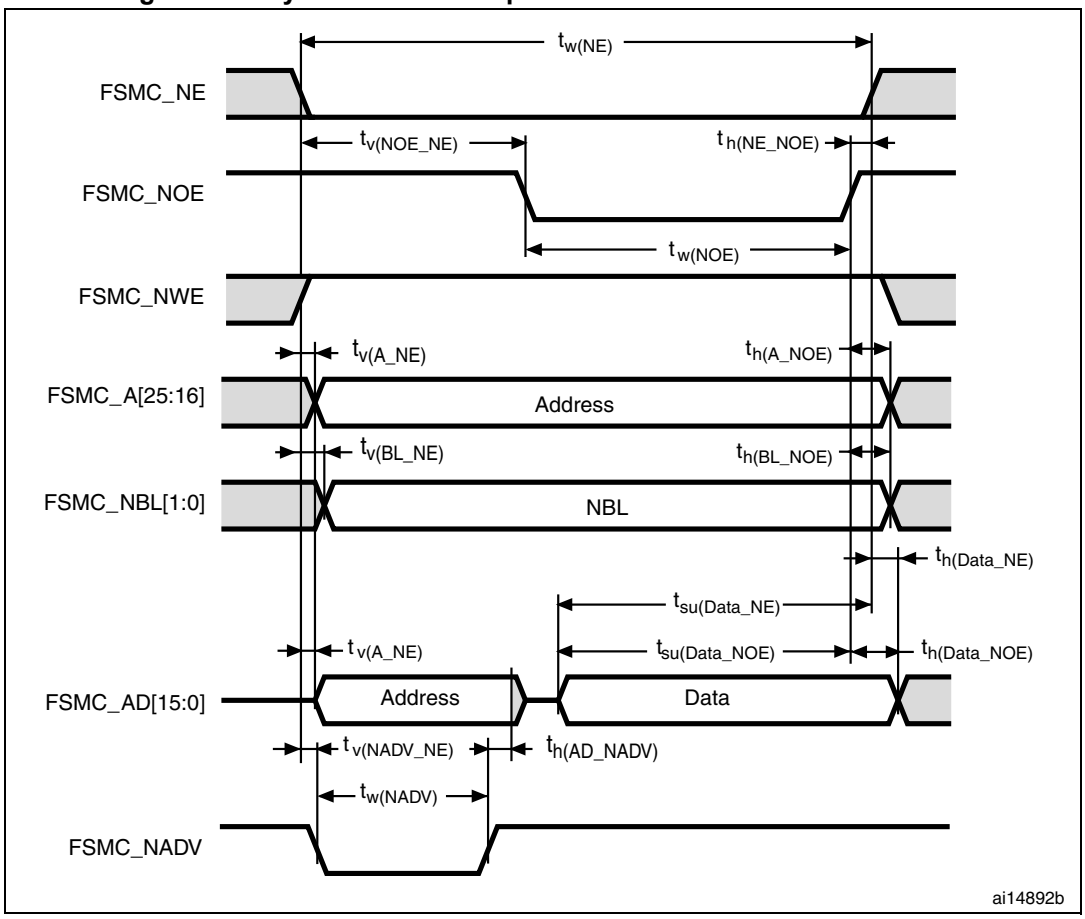


Table 33. Asynchronous multiplexed PSRAM/NOR read timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FSMC_NE low time	$7t_{HCLK} – 2$	$7t_{HCLK} + 2$	ns
$t_{v(NOE\_NE)}$	FSMC_NEx low to FSMC_NOE low	$3t_{HCLK} – 0.5$	$3t_{HCLK} + 1.5$	ns
$t_{w(NOE)}$	FSMC_NOE low time	$4t_{HCLK} – 1$	$4t_{HCLK} + 2$	ns
$t_{h(NE\_NOE)}$	FSMC_NOE high to FSMC_NE high hold time	–1	-	ns
$t_{v(A\_NE)}$	FSMC_NEx low to FSMC_A valid	-	0	ns
$t_{v(NADV\_NE)}$	FSMC_NEx low to FSMC_NADV low	3	5	ns
$t_{w(NADV)}$	FSMC_NADV low time	t_{HCLK} –1.5	t_{HCLK} + 1.5	ns
$t_{h(AD\_NADV)}$	FSMC_AD (address) valid hold time after FSMC_NADV high	t_{HCLK}	-	ns
$t_{h(A\_NOE)}$	Address hold time after FSMC_NOE high	t_{HCLK} -2	-	ns
$t_{h(BL\_NOE)}$	FSMC_BL hold time after FSMC_NOE high	0	-	ns
$t_{v(BL\_NE)}$	FSMC_NEx low to FSMC_BL valid	-	0	ns
$t_{su(Data\_NE)}$	Data to FSMC_NEx high setup time	$2t_{HCLK} + 24$	-	ns
$t_{su(Data\_NOE)}$	Data to FSMC_NOE high setup time	$2t_{HCLK} + 25$	-	ns

Table 35. Synchronous multiplexed NOR/PSRAM read timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FSMC_CLK period	27.7	-	ns
$t_{d(CLKL-NExL)}$	FSMC_CLK low to FSMC_NEx low (x = 0...2)	-	1.5	ns
$t_{d(CLKL-NExH)}$	FSMC_CLK low to FSMC_NEx high (x = 0...2)	2	-	ns
$t_{d(CLKL-NADVL)}$	FSMC_CLK low to FSMC_NADV low	-	4	ns
$t_{d(CLKL-NADVH)}$	FSMC_CLK low to FSMC_NADV high	5	-	ns
$t_{d(CLKL-AV)}$	FSMC_CLK low to FSMC_Ax valid (x = 16...25)	-	0	ns
$t_{d(CLKL-AIV)}$	FSMC_CLK low to FSMC_Ax invalid (x = 16...25)	2	-	ns
$t_{d(CLKL-NOEL)}$	FSMC_CLK low to FSMC_NOE low	-	1	ns
$t_{d(CLKL-NOEH)}$	FSMC_CLK low to FSMC_NOE high	1.5	-	ns
$t_{d(CLKL-ADV)}$	FSMC_CLK low to FSMC_AD[15:0] valid	-	12	ns
$t_{d(CLKL-ADIV)}$	FSMC_CLK low to FSMC_AD[15:0] invalid	0	-	ns
$t_{su(ADV-CLKH)}$	FSMC_A/D[15:0] valid data before FSMC_CLK high	6	-	ns
$t_{h(CLKH-ADV)}$	FSMC_A/D[15:0] valid data after FSMC_CLK high	0	-	ns
$t_{su(NWAITV-CLKH)}$	FSMC_NWAIT valid before FSMC_CLK high	8	-	ns
$t_{h(CLKH-NWAITV)}$	FSMC_NWAIT valid after FSMC_CLK high	2	-	ns

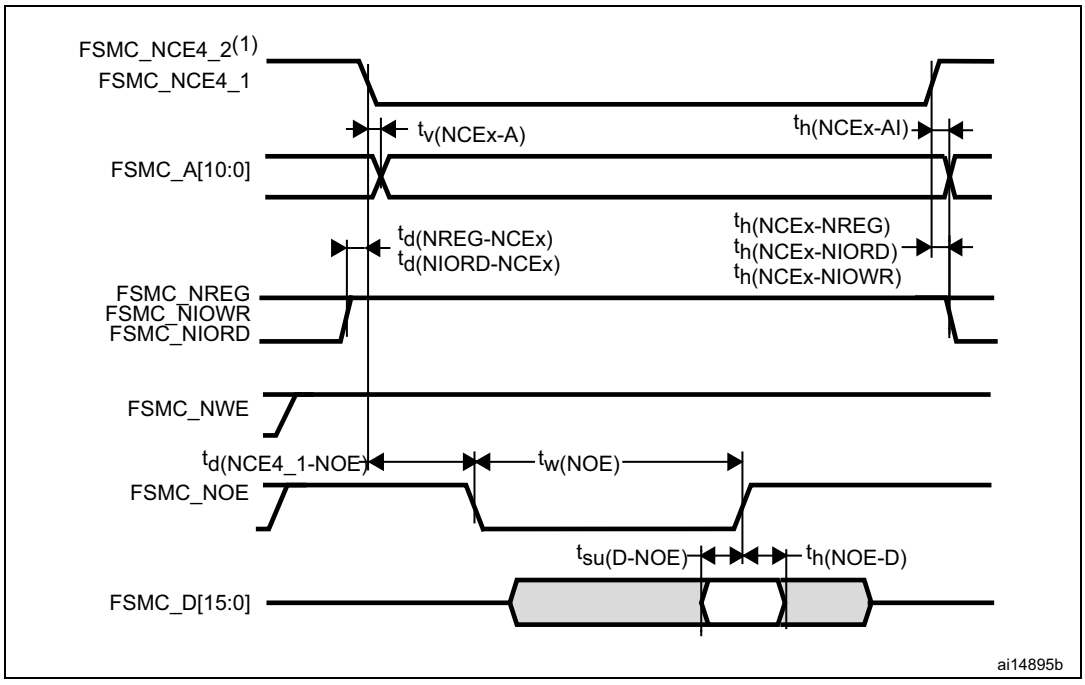
1. C_L = 15 pF.
2. Guaranteed by characterization results.

PC Card/CompactFlash controller waveforms and timings

Figure 32 through *Figure 37* represent synchronous waveforms and *Table 39* provides the corresponding timings. The results shown in this table are obtained with the following FSMC configuration:

- COM.FSMC_SetupTime = 0x04;
- COM.FSMC_WaitSetupTime = 0x07;
- COM.FSMC_HoldSetupTime = 0x04;
- COM.FSMC_HiZSetupTime = 0x00;
- ATT.FSMC_SetupTime = 0x04;
- ATT.FSMC_WaitSetupTime = 0x07;
- ATT.FSMC_HoldSetupTime = 0x04;
- ATT.FSMC_HiZSetupTime = 0x00;
- IO.FSMC_SetupTime = 0x04;
- IO.FSMC_WaitSetupTime = 0x07;
- IO.FSMC_HoldSetupTime = 0x04;
- IO.FSMC_HiZSetupTime = 0x00;
- TCLRSetupTime = 0;
- TARSetupTime = 0;

Figure 32. PC Card/CompactFlash controller waveforms for common memory read access



1. FSMC_NCE4_2 remains high (inactive during 8-bit access.

Figure 37. PC Card/CompactFlash controller waveforms for I/O space write access

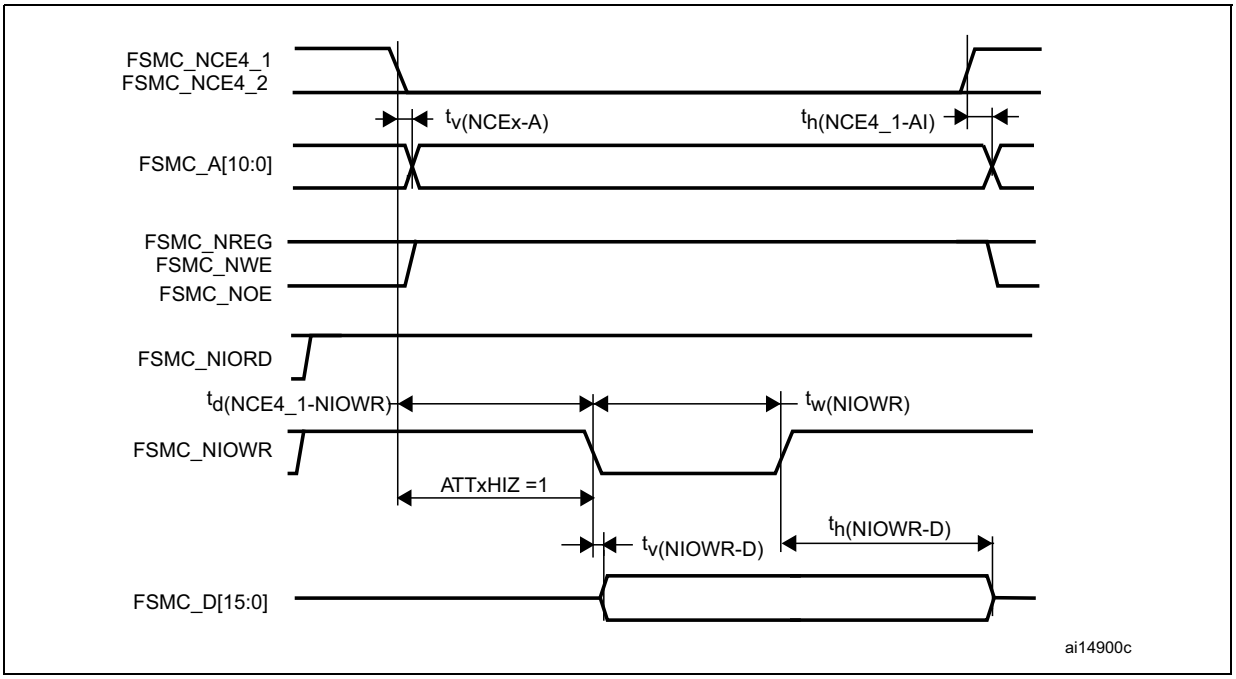
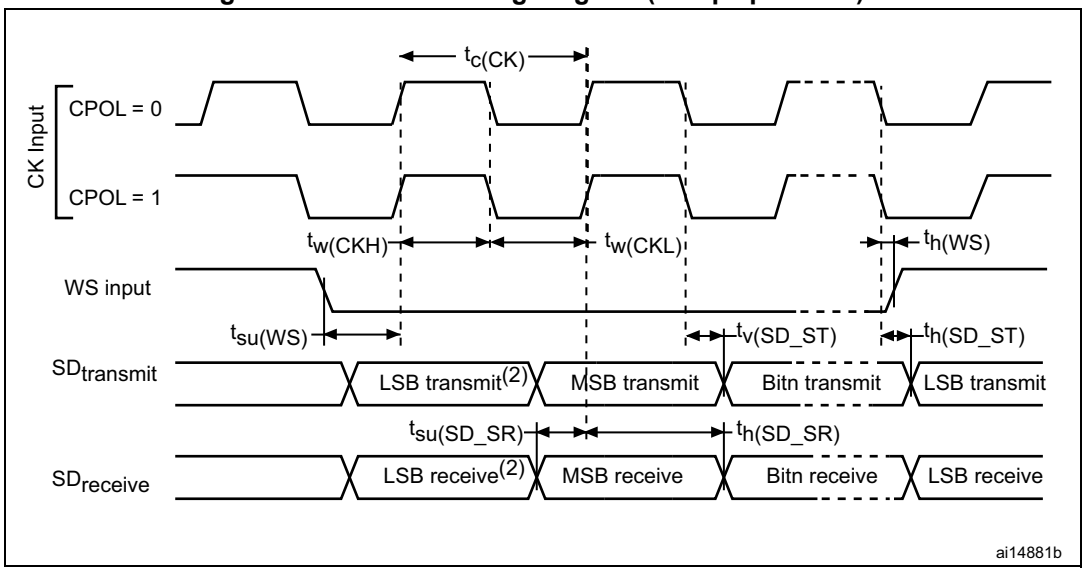


Table 39. Switching characteristics for PC Card/CF read and write cycles(1)(2)

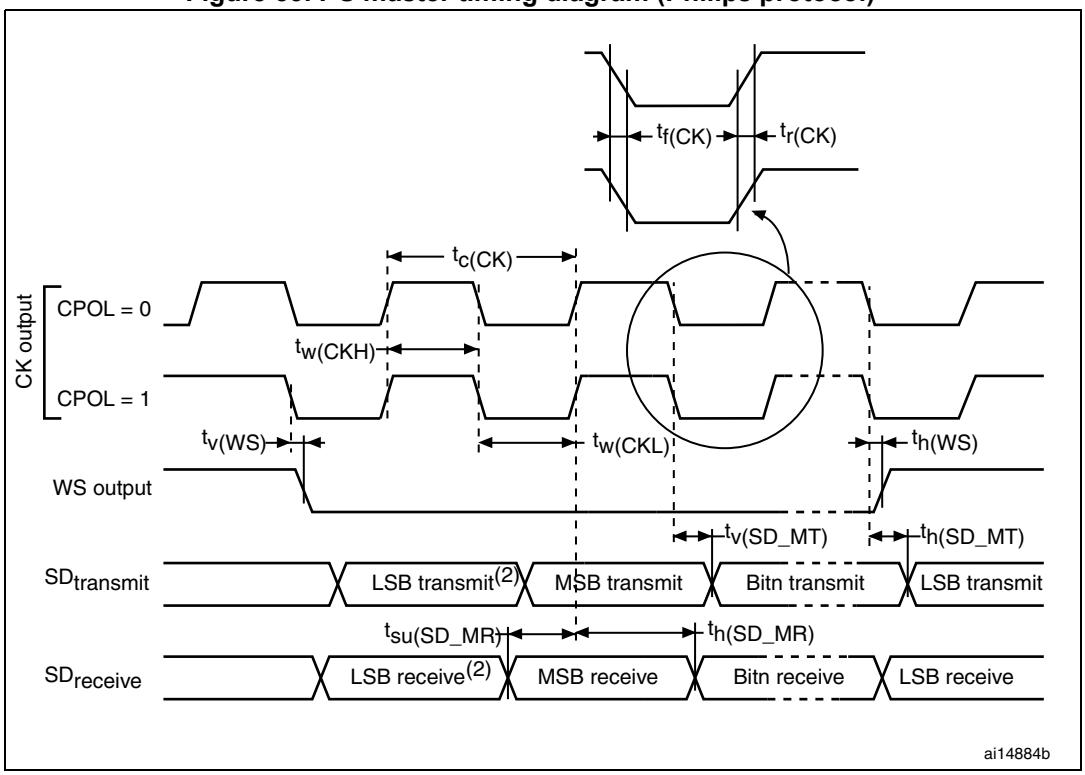
Symbol	Parameter	Min	Max	Unit
$t_{v(NCEx-A)}$ $t_{v(NCE4\_1-A)}$	FSMC_NCEx low (x = 4_1/4_2) to FSMC_Ay valid (y = 0...10) FSMC_NCE4_1 low (x = 4_1/4_2) to FSMC_Ay valid (y = 0...10)	-	0	ns
$t_{h(NCEx-AI)}$ $t_{h(NCE4\_1-AI)}$	FSMC_NCEx high (x = 4_1/4_2) to FSMC_Ax invalid (x = 0...10) FSMC_NCE4_1 high (x = 4_1/4_2) to FSMC_Ax invalid (x = 0...10)	2.5	-	ns
$t_{d(NREG-NCEx)}$ $t_{d(NREG-NCE4\_1)}$	FSMC_NCEx low to FSMC_NREG valid FSMC_NCE4_1 low to FSMC_NREG valid	-	5	ns
$t_{h(NCEx-NREG)}$ $t_{h(NCE4\_1-NREG)}$	FSMC_NCEx high to FSMC_NREG invalid FSMC_NCE4_1 high to FSMC_NREG invalid	t_{HCLK} + 3	-	ns
$t_{d(NCE4\_1-NOE)}$	FSMC_NCE4_1 low to FSMC_NOE low	-	$5t_{HCLK}$ + 2	ns
$t_{w(NOE)}$	FSMC_NOE low width	$8t_{HCLK}$ –1.5	$8t_{HCLK}$ + 1	ns
$t_{d(NOE-NCE4\_1}$	FSMC_NOE high to FSMC_NCE4_1 high	$5t_{HCLK}$ + 2	-	ns
$t_{su(D-NOE)}$	FSMC_D[15:0] valid data before FSMC_NOE high	25	-	ns
$t_{h(NOE-D)}$	FSMC_D[15:0] valid data after FSMC_NOE high	15	-	ns
$t_{w(NWE)}$	FSMC_NWE low width	$8t_{HCLK}$ – 1	$8t_{HCLK}$ + 2	ns
$t_{d(NWE-NCE4\_1)}$	FSMC_NWE high to FSMC_NCE4_1 high	$5t_{HCLK}$ + 2	-	ns
$t_{d(NCE4\_1-NWE)}$	FSMC_NCE4_1 low to FSMC_NWE low	-	$5t_{HCLK}$ + 1.5	ns
$t_{v(NWE-D)}$	FSMC_NWE low to FSMC_D[15:0] valid	-	0	ns
$t_{h(NWE-D)}$	FSMC_NWE high to FSMC_D[15:0] invalid	$11t_{HCLK}$	-	ns
$t_{d(D-NWE)}$	FSMC_D[15:0] valid before FSMC_NWE high	$13t_{HCLK}$	-	ns

Figure 52. I²S slave timing diagram (Philips protocol)(1)



1. Measurement points are done at CMOS levels: $0.3 \times V_{DD}$ and $0.7 \times V_{DD}$.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Figure 53. I²S master timing diagram (Philips protocol)(1)



1. Guaranteed by characterization results.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

1. Guaranteed by characterization results.
2. Guaranteed by design.
3. V_{REF+} can be internally connected to V_{DDA} and V_{REF-} can be internally connected to V_{SSA}, depending on the package. Refer to *Section 3: Pinouts and pin descriptions* for further details.
4. For external triggers, a delay of $1/f_{PCLK2}$ must be added to the latency specified in *Table 59*.

Equation 1: R_{AIN} max formula

$$R_{AIN} < \frac{T_S}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The formula above (*Equation 1*) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).

Table 60. R_{AIN} max for f_{ADC} = 14 MHz(1)

T_s (cycles)	t_S (µs)	R_{AIN} max (kΩ)
1.5	0.11	0.4
7.5	0.54	5.9
13.5	0.96	11.4
28.5	2.04	25.2
41.5	2.96	37.2
55.5	3.96	50
71.5	5.11	NA
239.5	17.1	NA

1. Guaranteed by design.

Table 61. ADC accuracy - limited test conditions(1)(2)

Symbol	Parameter	Test conditions	Typ	Max(3)	Unit
ET	Total unadjusted error	f_{PCLK2} = 56 MHz, f_{ADC} = 14 MHz, R_{AIN} < 10 kΩ, V_{DDA} = 3 V to 3.6 V T_A = 25 °C Measurements made after ADC calibration V_{REF+} = V_{DDA}	±1.3	±2	LSB
EO	Offset error		±1	±1.5	
EG	Gain error		±0.5	±1.5	
ED	Differential linearity error		±0.7	±1	
EL	Integral linearity error		±0.8	±1.5	

1. ADC DC accuracy values are measured after internal calibration.
2. ADC Accuracy vs. Negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
   Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in *Section 5.3.14* does not affect the ADC accuracy.
3. Guaranteed by characterization results.

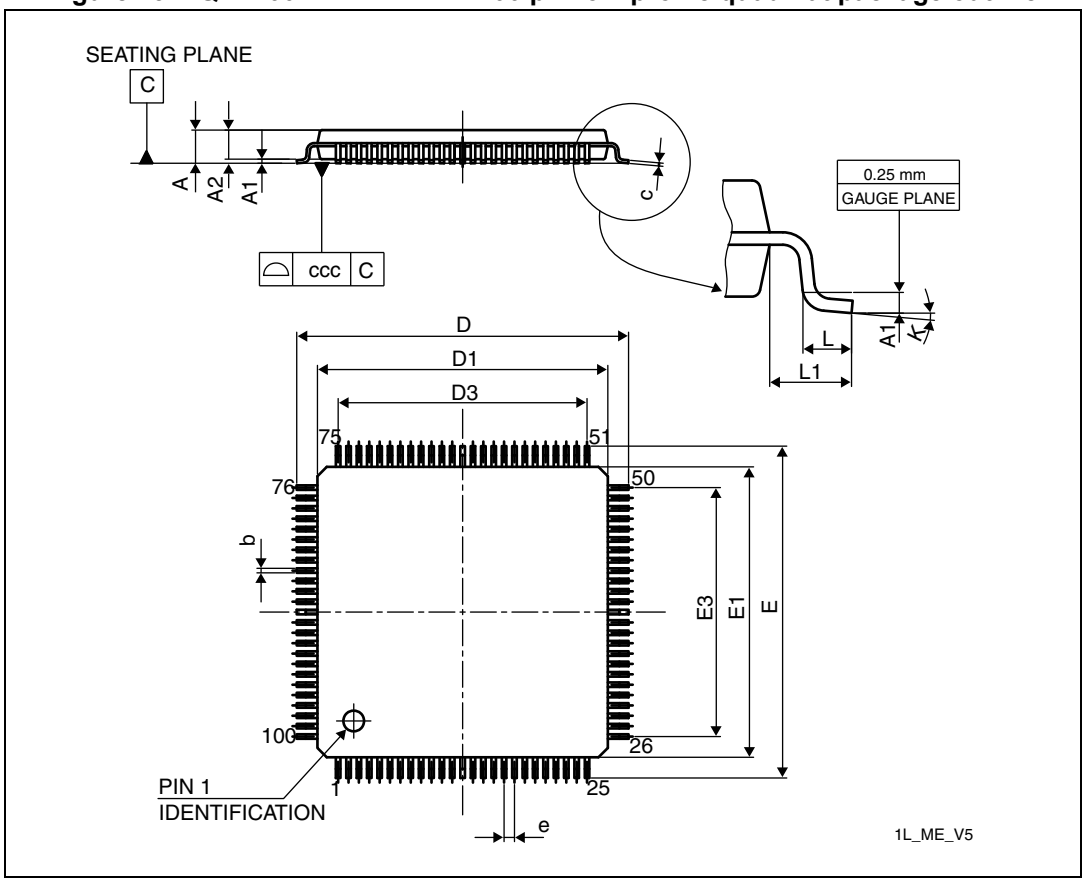
5.3.20 DAC electrical specifications

Table 63. DAC characteristics

Symbol	Parameter	Min	Typ	Max	Unit	Comments
V_{DDA}	Analog supply voltage	2.4	-	3.6	V	-
V_{REF+}	Reference supply voltage	2.4	-	3.6	V	V_{REF+} must always be below V_{DDA}
V_{SSA}	Ground	0	-	0	V	-
R_{LOAD} (1)	Resistive load with buffer ON	5	-	-	kΩ	-
R_O (2)	Impedance output with buffer OFF	-	-	15	kΩ	When the buffer is OFF, the Minimum resistive load between DAC_OUT and V_{SS} to have a 1% accuracy is 1.5 MΩ
C_{LOAD} (1)	Capacitive load	-	-	50	pF	Maximum capacitive load at DAC_OUT pin (when the buffer is ON).
DAC_OUT min (1)	Lower DAC_OUT voltage with buffer ON	0.2	-	-	V	It gives the maximum output excursion of the DAC. It corresponds to 12-bit input code (0x0E0) to (0xF1C) at V_{REF+} = 3.6 V and (0x155) and (0xEAB) at V_{REF+} = 2.4 V
DAC_OUT max (1)	Higher DAC_OUT voltage with buffer ON	-	-	V_{DDA} – 0.2	V	
DAC_OUT min (1)	Lower DAC_OUT voltage with buffer OFF	-	0.5	-	mV	It gives the maximum output excursion of the DAC.
DAC_OUT max (1)	Higher DAC_OUT voltage with buffer OFF	-	-	V_{REF+} – 1LSB	V	
$I_{DDVREF+}$	DAC DC current consumption in quiescent mode (Standby mode)	-	-	220	µA	With no load, worst code (0xF1C) at V_{REF+} = 3.6 V in terms of DC consumption on the inputs
I_{DDA}	DAC DC current consumption in quiescent mode (3)	-	-	380	µA	With no load, middle code (0x800) on the inputs
		-	-	480	µA	With no load, worst code (0xF1C) at V_{REF+} = 3.6 V in terms of DC consumption on the inputs
DNL (4)	Differential non linearity Difference between two consecutive code-1LSB)	-	-	±0.5	LSB	Given for the DAC in 10-bit configuration
		-	-	±2	LSB	Given for the DAC in 12-bit configuration
INL (3)	Integral non linearity (difference between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 1023)	-	-	±1	LSB	Given for the DAC in 10-bit configuration
		-	-	±4	LSB	Given for the DAC in 12-bit configuration

6.5 LQFP100 package information

Figure 73. LQFP100 – 14 x 14 mm 100 pin low-profile quad flat package outline



1. Drawing is not to scale.

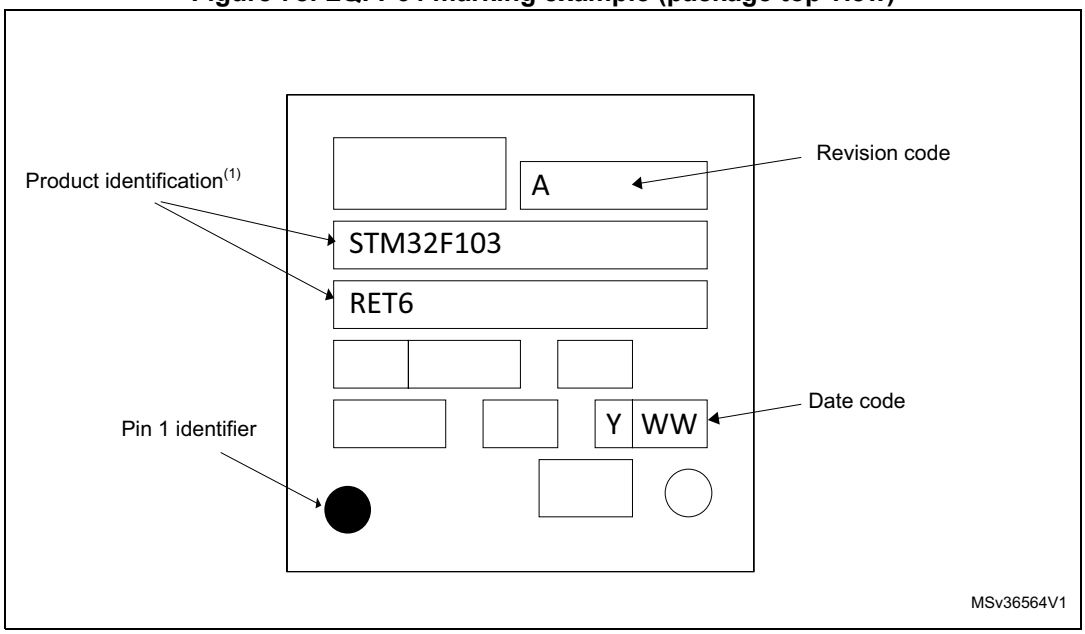
Table 72. LQPF100 – 14 x 14 mm 100-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3	-	12.000	-	-	0.4724	-
E	15.800	16.000	16.200	0.6220	0.6299	0.6378
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591
E3	-	12.000	-	-	0.4724	-

Device marking for LQFP64 package

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Figure 78. LQFP64 marking example (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.